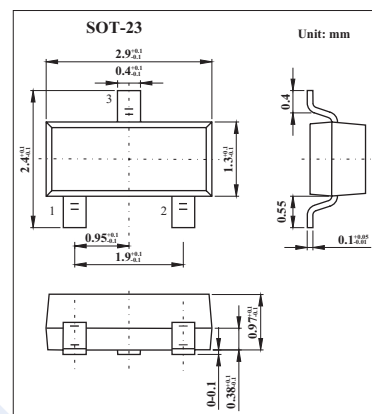
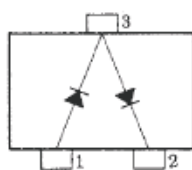


Schottky Barrier Diode

1SS358

■ Features

- Small interterminal capacitance
- Low forward voltage and excellent detection efficiency
- High breakdown voltage



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
peak reverse voltage	V_R	55	V
Forward current	I_F	10	mA
Power dissipation	P	150	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 1\text{ mA}$			0.35	V
Reverse voltage	V_R	$I_R = 100\text{ }\mu\text{A}$	55			V
Forward Current	I_F	$V_F = 1\text{ V}$	10			mA
Reverse current	I_R	$V_R = 40\text{ V}$			50	μA
Interterminal capacitance	C	$V_R = 0, f = 1.0\text{ MHz}$		0.45		pF

■ Marking

Marking	DH
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